

MBRD5H100T4G

Schottky Power Rectifier, Switch-mode, 5.0 A, 100 V

Product Overview

For complete documentation, see the data sheet.

The Schottky Rectifier employs the Schottky Barrier principle in a large metal to silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlay contact. It is ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes and polarity protection diodes.

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Short Heat Sink Tab Manufactured - Not Sheared!
- NBRD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable



Applications

- Power Supplies

End Products

- Power Supplies

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Configuration	V _{RRM} Min (V)	V _F Max (V)	I _{RM} Max (µA)	I _{O(rec)Max} (A)	I _{FSM} Max (A)	t _{rr} Max (ns)	C _j Max (pF)	Package Type
MBRD5H100T4G	0.4048	 	Active	Single	100	0.71	3.5	5	105	-	-	DPAK-3